

Silicon NPN Power Transistors

2SD1632

DESCRIPTION

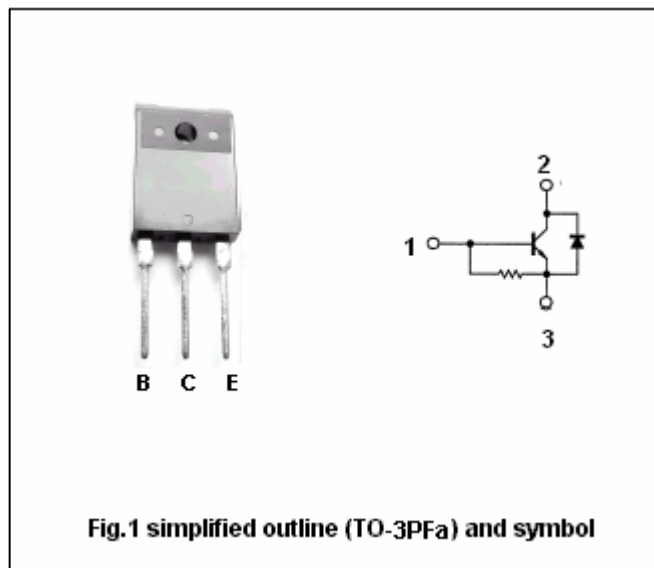
- With TO-3PFa package
- High voltage ,high speed
- Built-in damper diode
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |



Absolute maximum ratings(Ta=25)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|--------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _C | Collector current | | 4 | A |
| I _{CM} | Collector current-peak | | 15 | A |
| I _{BM} | Base current | | 3.5 | A |
| P _C | Collector power dissipation | T _C =25 | 70 | W |
| T _j | Junction temperature | | 130 | |
| T _{stg} | Storage temperature | | -55~130 | |

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CHARACTERISTICS

T_j=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =500mA ; I _C =0 | 5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =3A ; I _B =1A | | | 1.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =3A ; I _B =1A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =750V; I _E =0 | | | 50 | μ A |
| | | V _{CB} =1500V; I _E =0 | | | 1 | mA |
| h _{FE} | DC current gain | I _C =3A ; V _{CE} =10V | 5 | | 15 | |
| V _F | Diode forward voltage | I _C =-4A | | | 2.2 | V |

Switching times

| | | | | | | |
|------------------|--------------|---|---|--|-----|-----|
| t _{stg} | Storage time | I _C =3A I _{Bend} =1A; L _{Leak} =5 μ H | 4 | | 9 | μ s |
| t _f | Fall time | | | | 0.8 | μ s |

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PACKAGE OUTLINE

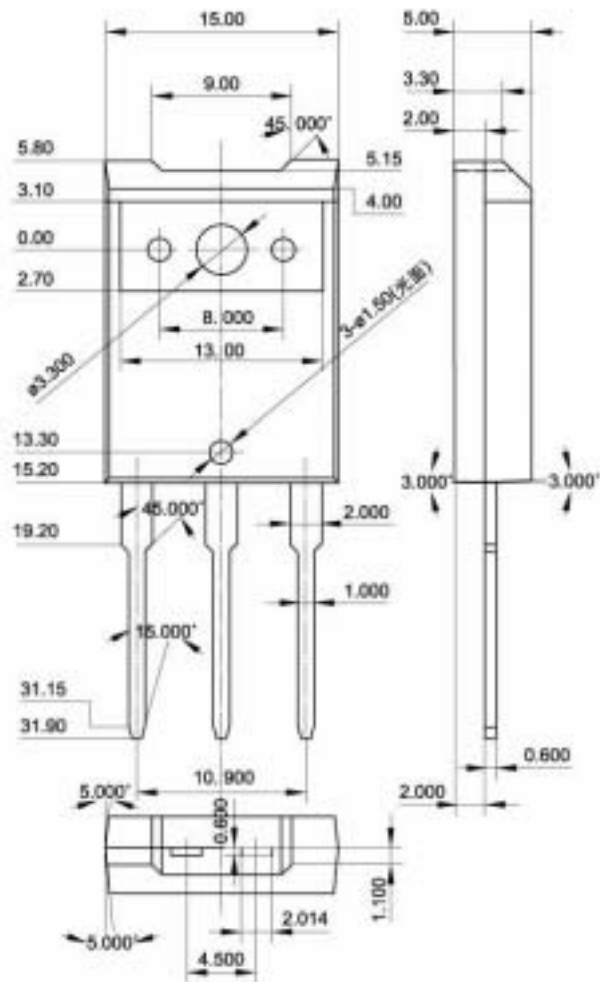


Fig.2 Outline dimensions (unindicated tolerance: ± 0.30mm)